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(Rev. 8-83)U.S. Department of Commerce
Patent and Trademark Office

Attorney Docket No. 0756-958

Serial No. 08/183,800

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Shunpei YAMAZAKI

Filing Date: 01/21/94

Group: 2508

U. S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
SWC	4,266,986	05/12/81	BENTON et al.			11/29/79
	5,210,050	05/11/93	YAMAZAKI et al.			10/11/91
	5,272,361	12/21/93	YAMAZAKI, Shunpei			11/01/91
	4,959,700	09/25/90	YAMAZAKI, Shunpei			02/03/88
	5,306,651	04/26/94	MASUMO et al.			05/10/91
	5,278,093	01/11/94	YONEHARA, Takao			07/29/92
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	4,897,360	01/30/90	GUCKEL et al.			12/09/87
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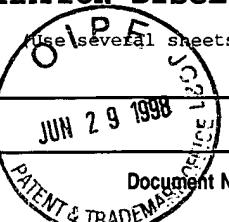
	Document Number	Date	Country	Class	Subclass	Translation Yes	Translation No
SWC	0 178 447	04/23/86	Europe	RECEIVED		X	
SWC	161 555 A	10/21/85	EP	JUL 08 1998		X	
SWC	2 103925	04/17/90	Japan	GROUP 2100		ABS	

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SWC	WOLF et al., "Silicon Processing For The VLSI Era", Vol I, Lattice Press, Sunset Beach, California, pp. 19-21.
SWC	SAMESHIMA et al., "XeCl Excimer Laser Annealing Used to Fabricate Poly-Si TFT's", Japanese Journal of Applied Physics, Vol. 28, No. 10, October 1989, pp. 1789-1793.
SWC	IWAMATSU et al., "Silicon-On-Sapphire M.O.S.F.E.T.S. Fabricated By Back-Surface Laser-Anneal Technology, Electronics Letters, Vol. 15, #25, pp. 827-828, December 1979.
SWC	SERA et al., "High Performance TFT's Fabricated by XeCl Excimer Laser Annealing of Hydrogenated Amorphous-Silicon Film", IEEE Transactions on Electron Devices, 36(1989), pp. 2868-2872.
SWC	KIANG et al., "Modification of Semiconductor Device Characteristics by Lasers", IBM, 1982, pp. 171-6.
SWC	PRESSLEY, "Excimer Laser Processing of Semiconductors", Lasers & Applications, May 1985, pp. 93-98.

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*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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<div style="text-align: center;">  JUN 29 1998 </div> U. S. PATENT DOCUMENTS							
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	4,891,330	01/02/90	GUHA et al.			03/28/88	
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				GROUP 2100			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
SWC	PUMMER, "Commercial Excimer Lasers", Scientific and Engineering Applications of Commercial Laser Devices", pp. 38-42.						
SWC	YÜKI et al., "A Full-Color LCD Addressed by Poly-Si TFT's Fabricated Below 450°C", IEE Transactions on Electron Devices, Vol. 36, No. 9, pp. 1934-7.						
SWC	MASUMO et al., "Low Temperature Fabrication of Poly-Si TFT by Laser Induced Crystallization of a-Si", Journal of Non-Crystalline Solids, Vol. 115, pp. 147-149.						
SWC	SAMESHIMA et al., "XeCl Excimer Laser Annealing Used to Fabricate Poly-Si TFT's", Materials Research Society Symposia, Vol. 71, 1986, pp. 435-440.						
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	4,862,237	08/29/89	MOROZUMI, Shinji			10/04/88	
	5,132,821	07/21/92	NICHOLAS, Keith H.			07/26/90	
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